

**In the Claims:**

Please amend claim 11. Please cancel claim 36. The claims are as follows.

**Claims 1-9 (CANCELED)**

10. (PREVIOUSLY PRESENTED) A method for forming an electronic structure, comprising the following steps:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

forming a mineral layer on the metallic plate after the step of providing a metallic plate is performed, including forming a first portion of the mineral layer on a first surface of the metallic plate and forming a second portion of the mineral layer on a second surface of the metallic plate, wherein the first surface of the metallic plate is about perpendicular to the second surface of the metallic plate; and

forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed, including forming a first portion of the adhesion promoter layer on the first portion of the mineral layer and forming a second portion of the adhesion promoter layer on the second portion of the mineral layer.

11. (CURRENTLY AMENDED) ~~A method for forming an electronic structure, comprising the following steps:~~

~~providing a metallic plate such that all exterior surfaces of the metallic plate are exposed~~

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~~to an ambient atmosphere;~~

~~forming a mineral layer on the metallic plate after the step of providing a metallic plate is performed; and~~

~~forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed~~ The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a mineral selected from the group consisting of silicon dioxide, silicon nitride, and silicon carbide.

12. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 50 angstroms and about 2000 angstroms.

13. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes sputtering the mineral layer on a clean surface of the metallic plate.

14. (PREVIOUSLY PRESENTED) The method of claim 10, wherein providing the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, aluminum, titanium, copper, copper coated with nickel, and copper coated with chrome.

15. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter

selected from the group consisting of a titanate, a zirconate, and an aluminate.

16. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having a silane from the group consisting of 3-glycidoxypropyltrimethoxysilane, 3-glycidoxypropyltriethoxysilane, 3-(2-aminoethyl)propyltrimethoxysilane, and 3-(2-aminoethyl)propyltrimethoxysilane.

17. (ORIGINAL) The method of claim 10, further comprising:

providing an electronic assembly;

providing an adhesive material;

coupling the metallic plate to the electronic assembly by interfacing the adhesive material between the adhesion promoter layer and the electronic assembly;

providing an electronic carrier;

coupling the electronic assembly to the electronic carrier; and

coupling the metallic plate to the electronic carrier by interfacing the adhesive material between the adhesion promoter layer and the electronic carrier.

18-19. (CANCELED)

20. (PREVIOUSLY PRESENTED) The method of claim 10, further comprising bonding the adhesion promoter layer to a structural adhesive.

21. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the adhesion promoter layer has a thickness between 1 monolayer and about 50 monolayers.
22. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in crystalline form.
23. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in amorphous form.
24. (CANCELED)
25. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 100 angstroms and about 1000 angstroms.
26. (CANCELED)
27. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter comprising a silane.

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28. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the step of forming an adhesion promoter layer comprises covalently bonding the adhesion promoter layer to the mineral layer.

29. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the step of forming an adhesion promoter layer comprises bonding the adhesion promoter layer to the mineral layer such that said bonding to the mineral layer is moisture resistant.

30-32.(CANCELED)

33. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the step of forming the mineral layer on the metallic plate comprises forming the mineral layer on first and second exposed surface of said exposed surfaces, and wherein said first and second exposed surfaces are not coplanar.

34. (PREVIOUSLY PRESENTED) The method of claim 10,

wherein the step of forming a mineral layer on the metallic plate further includes forming a third portion of the mineral layer on a third surface of the metallic plate,

wherein the third surface of the metallic plate is about perpendicular to the second surface of the metallic plate,

wherein the third surface of the metallic plate is about parallel to the first surface of the metallic plate, and

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wherein the step of forming an adhesion promoter layer on the mineral layer further includes forming a third portion of the adhesion promoter layer on the third portion of the mineral layer.

35. (PREVIOUSLY PRESENTED) The method of claim 17, wherein the electronic assembly is a semiconductor chip, and wherein the electronic carrier is a chip carrier.

36. (CANCELED)